



JA04001000P47; 400 MHz – 1000 MHz 50W AMPLIFIER

- Solid-state Class AB design
- GaN on SiC Transistors
- High reliability and ruggedness
- Ultra Small Dimensions & Ultra Light Weight
- Forward/Reflected Power Monitorings
- Temperature and Current Monitorings
- Fast Switching Capability



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	400-1000 MHz
Output Power:	50 W min. CW
Nominal Gain:	47 dB
Gain Flatness:	± 1.5 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 for 1 min.
DC Supply Voltage:	32 V
DC Current:	4.8 A Avg
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F/G
Vibration:	MIL-STD-810F/G

INTERFACES

RF Input:	SMA Female
RF Output:	SMA Female
9-PIN DSUB:	1) Temperature
	2) Current
	3) Forward Power
	4) 32V
	5) 32V
	6) Reverse Power
	7) Enable
	8) GND
	9) GND

MECHANICAL SPECIFICATIONS

Size (mm) : 135 x 75 x 24
Weight : 460 gr.

